

8 A Snubberless™ Triac

Datasheet - production data

Features

- High static and dynamic commutation
- Package is RoHS (2002/95/EC) compliant
- High surge current
- ECOPACK®2 compliant component
- Complies with UL standards (File ref: E81734)

Applications

- General purpose AC switching
- Motor control circuits in power tools
- Home appliances
- Lighting

Description

The T830-8FP Triac can be used for the on/off function in general purpose AC switching where high commutation capability is required.

Provides insulation rated at 1500 V rms.

This is information on a product in full production.

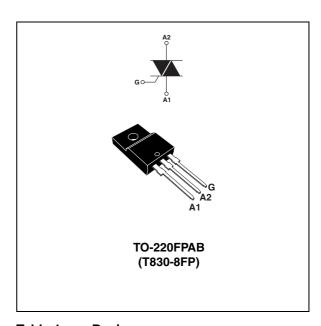


Table 1. Device summary

Symbol	Value	Unit
I _{T(rms)}	8	Α
V_{DRM}, V_{RRM}	800	V
V _{DSM} , V _{RSM}	900	V
I _{GT}	30	mA

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Characteristics T830-8FP

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Table 2. Absolute ratings (limiting values)

Symbol	Parameter			Value	Unit
I _{T(rms)}	On-state rms current (full sine wave)	T _c = 95 °C	8	Α
l	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	80	Α
I _{TSM}	current (full cycle, T_j initial = 25 °C)	F = 60 Hz	t = 16.7 ms	84	^
l ² t	I ² t Value for fusing	$t_p = 10 \text{ ms}$		42	A ² s
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	F = 120 Hz	T _j = 125 °C	100	A/μs
V _{DSM} , V _{RSM}	Non repetitive surge peak on-state voltage	t _p = 10 ms	T _j = 25 °C	900	٧
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 125 °C	4	Α
P _{G(AV)}	Average gate power dissipation $T_j = 125 ^{\circ}\text{C}$			1	W
T _{stg} T _j	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 125	°C
TL	Lead temperature for soldering during 10 s (at 4 mm from case)		260	°C	
V _{ins}	Insulation rms voltage, 1 minute			1500	V

Table 3. Electrical characteristics ($T_i = 25$ °C, unless otherwise specified)

Symbol	Test conditions Quadrant			Value	Unit
I _{GT} ⁽¹⁾	$V_{\rm D} = 12 \text{ V}, R_{\rm L} = 30 \Omega$	1 - 11 - 111	Max.	30	mA
V _{GT}	VD = 12 V, NL = 30 12	1 - 11 - 111		1.3	V
V _{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 125 \text{ °C}$ I - II - III		Min.	0.2	V
I _H ⁽²⁾	I _T = 250 mA		Max.	50	mA
ΙL	I _G = 1.2 I _{GT}	1 - 11 - 111	Max.	60	mA
dV/dt	V _D = 67%V _{DRM} , gate open	T _j = 125 °C	Min.	2500	V/µs
(dl/dt)c	Without snubber	T _j = 125 °C	Min.	10.0	A/ms

^{1.} Minimum $I_{\mbox{\scriptsize GT}}$ is guaranteed at 5% of $I_{\mbox{\scriptsize GT}}$ max.

^{2.} For both polarities of A2 referenced to A1.

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Table 4. Static characteristics

Symbol	Test conditions			Value	Unit
V _T ⁽¹⁾	$I_{TM} = 11 \text{ A}, t_p = 380 \ \mu \text{s}$	T _j = 25 °C	Max.	1.55	V
V _{t0} (1)	Threshold voltage	T _j = 125 °C	Max.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 125 °C	Max.	40	mΩ
I _{DRM} V _{DRM} = V _{RR}	V -V	T _j = 25 °C	Max.	5	μΑ
	VDRM = VRRM	T _j = 125 °C	iviax.	1	mA

^{1.} For both polarities of A2 referenced to A1.

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	3.5	°C/W
R _{th(j-a)}	Junction to ambient	60	°C/W

Figure 1. Maximum power dissipation versus Figure 2. On-state rms current versus case rms on-state current temperature

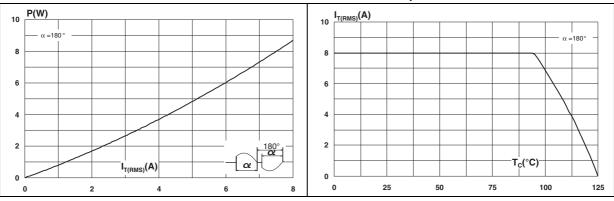
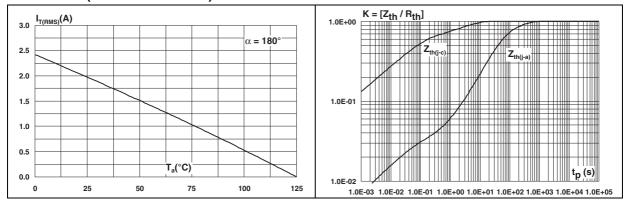


Figure 3. On-state rms current versus ambient temperature (free air convection)

Figure 4. Relative variation of thermal impedance versus pulse duration



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Figure 5. Relative variation of gate trigger current versus junction temperature (typical values)

Figure 6. Relative variation of gate trigger voltage versus junction temperature (typical values)

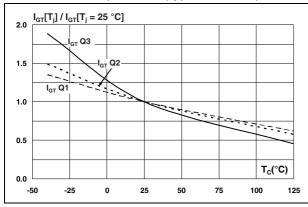
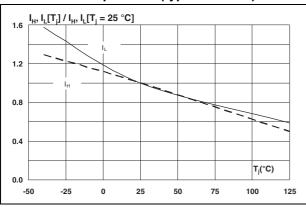


Figure 7. Relative variation of holding and latching current versus junction temperature (typical values)

Figure 8. Surge peak on-state current versus number of cycles



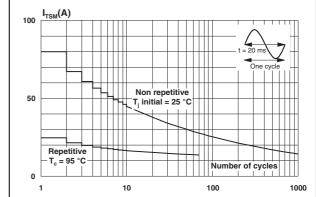
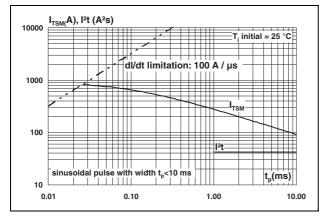
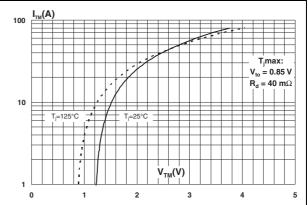


Figure 9. Non repetitive surge peak on-state Figure 10. current and corresponding value of I²T

igure 10. On-state characteristics (maximum values)





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Figure 11. Relative variation of critical rate of decrease of main current versus junction temperature Figure 12. Relative variation of static dV/dt immunity versus junction temperature (typical values)

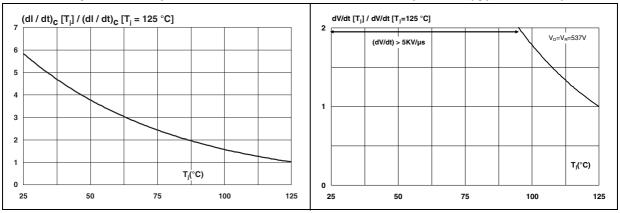
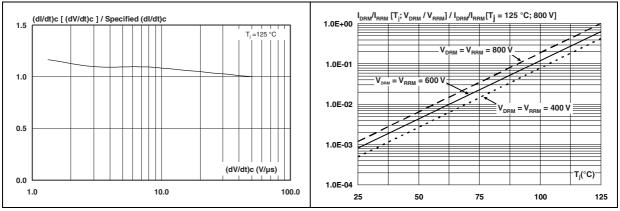


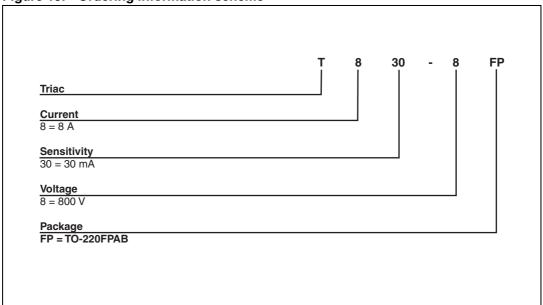
Figure 13. Relative variation of critical rate of Figure 14. decrease of main current versus reapplied dV/dt (typical values)

Figure 14. Relative variation of leakage current versus junction temperature



2 Ordering information scheme

Figure 15. Ordering information scheme

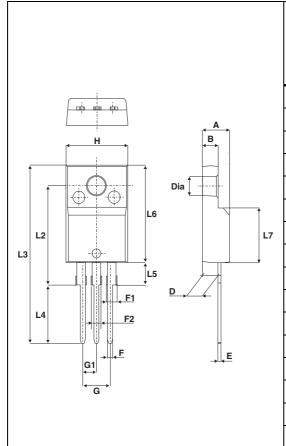


3 Package information

- Epoxy meets UL94, V0
- Recommended torque: 0.4 to 0.6 N⋅m

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Table 6. TO-220FPAB Dimensions



	Dimensions				
Ref.	Millim	neters	Inc	nes	
	Min.	Max.	Min.	Max.	
Α	4.4	4.6	0.173	0.181	
В	2.5	2.7	0.098	0.106	
D	2.5	2.75	0.098	0.108	
Е	0.45	0.70	0.018	0.027	
F	0.75	1	0.030	0.039	
F1	1.15	1.70	0.045	0.067	
F2	1.15	1.70	0.045	0.067	
G	4.95	5.20	0.195	0.205	
G1	2.4	2.7	0.094	0.106	
Н	10	10.4	0.393	0.409	
L2	16	16 Typ. 0.63 Typ.		Тур.	
L3	28.6	30.6	1.126 1.205		
L4	9.8	10.6	0.386	0.417	
L5	2.9	3.6	0.114	0.142	
L6	15.9	16.4	0.626	0.646	
L7	9.00	9.30	0.354	0.366	
Dia.	3.00	3.20	0.118	0.126	

Ordering information T830-8FP

4 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T830-8FP	T830-8FP	TO-220FPAB	2.0 g	50	Tube

5 Revision history

Table 8. Document revision history

Date	Revision	Changes
24-Sep-2012	1	Initial release.

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